Interface and oxide states induced by X-rays in Si/SiO$_2$ MOS like structures

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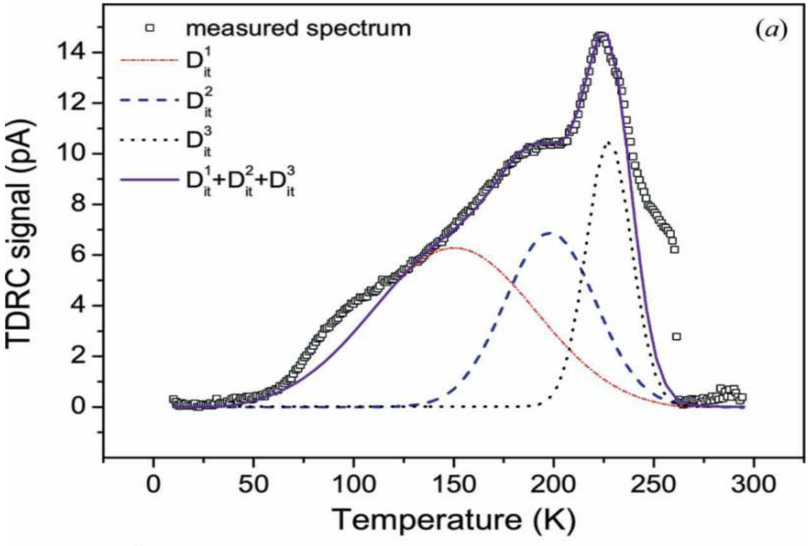

	D_{it}^1	D_{it}^2	D_{it}^3
σ [cm^2]	1.2×10^{-15}	5×10^{-17}	1.0×10^{-15}
peak energy [eV]	0.39	0.48	0.60
FWHM [eV]	0.26	0.13	0.071

J. Synchrotron Rad. (2012). 19, 340–346;
J. of Instrum. 7, C12012, 2012;